

Features

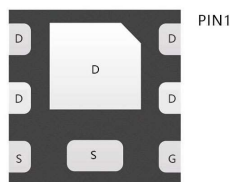
- Trench Power LV MOSFET technology
- Ultra low on-resistance with low gate charge

Product Summary

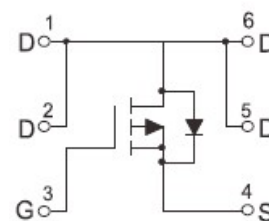
V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-20V	23.5mΩ@-4.5V	-11A
	40mΩ@-2.5V	

Application

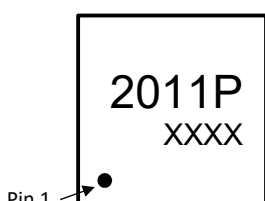
- PWM applications
- Battery charge in cellular handset
- Load switch



DFN2X2-6L bottom view



Schematic diagram



2011P: Device code
 XXXX: Code
 Solid dot: Pin1 indicator

Marking and pin assignment



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}C$ -11	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}C$ -44	A
I_D	Continuous Drain Current	$T_C=25^{\circ}C$ -11	A
P_D	Maximum Power Dissipation	$T_A=25^{\circ}C$ 4	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	31	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSM2011P	DFN2X2-6L	2011P	3,000	45,000	180,000	7"reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
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Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.45	--	-1.2	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-7.2A	--	15	23.5	mΩ
		V _{GS} =-2.5V, I _D =-6.4A	--	22	40	mΩ

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

C _{ISS}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	2700	--	pF
C _{OSS}	Output Capacitance		--	680	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	590	--	pF

Switching Characteristics

Q _g	Total Gate Charge	V _{DS} =-6V, I _D =-10A, V _{GS} =-4.5V	--	35	--	nC
Q _{gs}	Gate Source Charge		--	5	--	nC
Q _{gd}	Gate Drain Charge		--	10	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, I _D =-1A, V _{GS} =-4.5V, R _G =10Ω	--	11	--	nS
t _r	Turn-on Rise Time		--	35	--	nS
t _{d(off)}	Turn-Off Delay Time		--	30	--	nS
t _f	Turn-Off Fall Time		--	10	--	nS

Source- Drain Diode Characteristics

V _{SD}	Forward on voltage	T _J =25°C, I _S =-11A	--	--	-1.2	V
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Typical Operating Characteristics

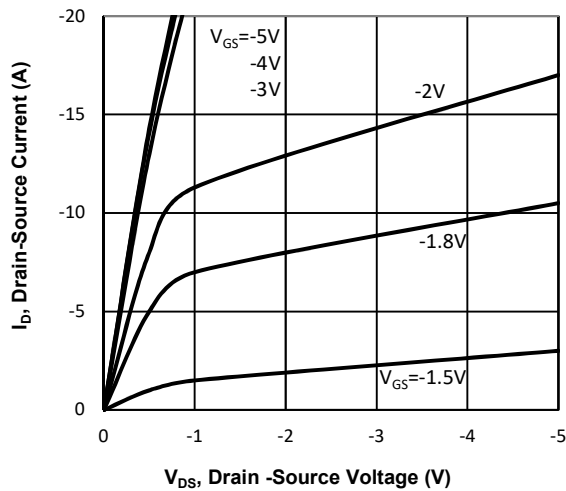


Fig1. Typical Output Characteristics

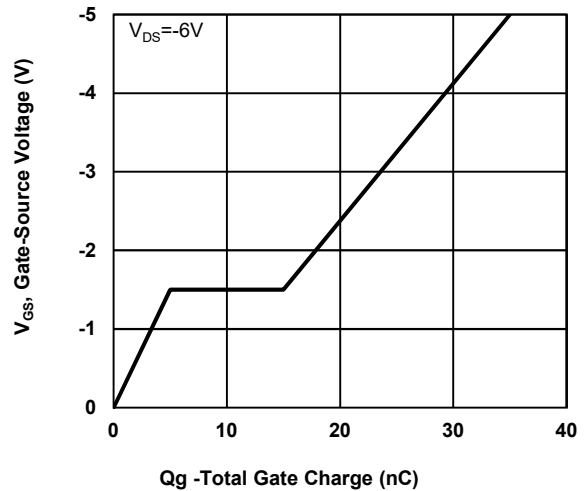


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

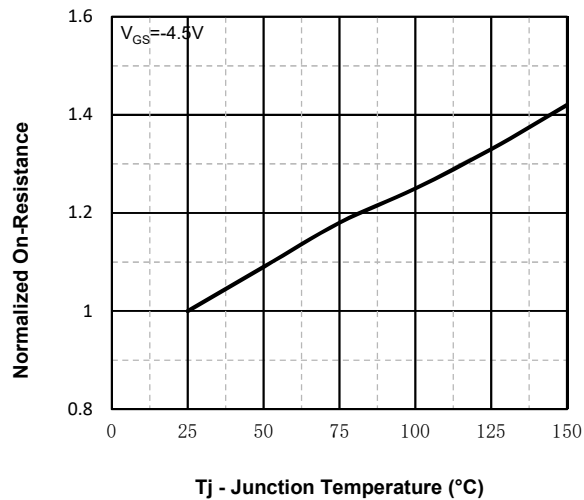


Fig3. Normalized On-Resistance Vs. Temperature

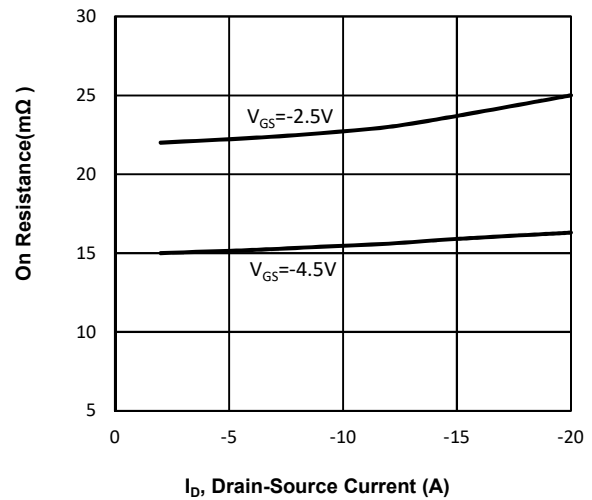


Fig4. On Resistance Vs. Drain-Source Current

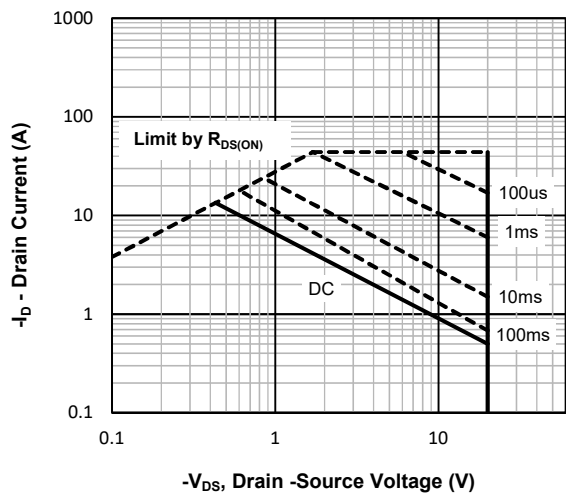


Fig5. Maximum Safe Operating Area

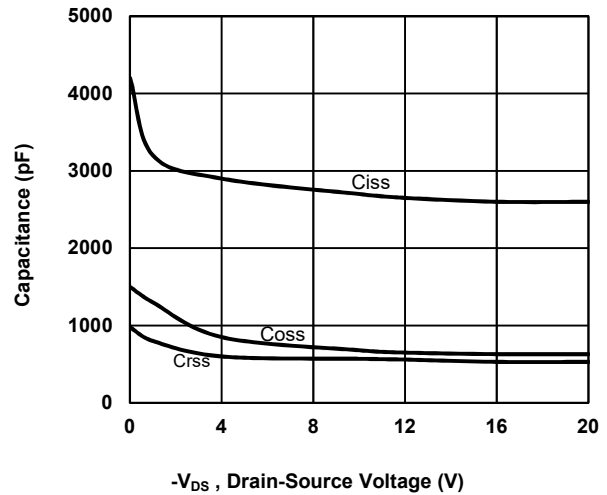
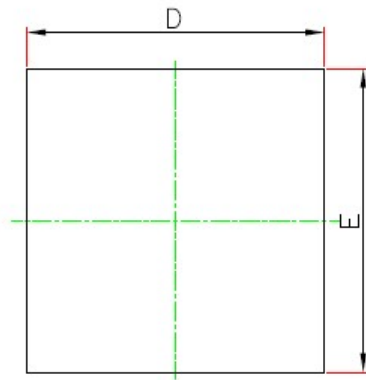
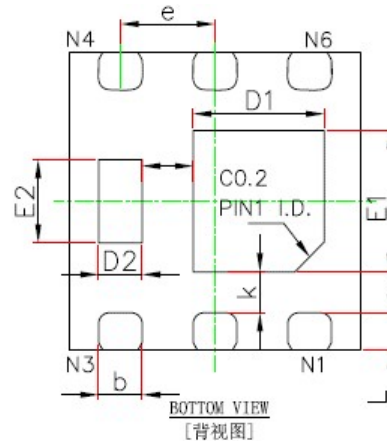


Fig6. Typical Capacitance Vs. Drain-Source Voltage

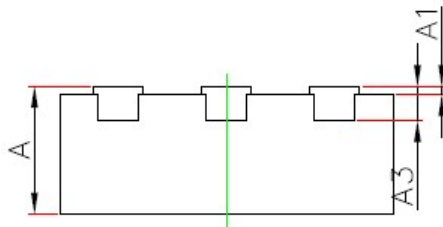
DFN2X2-6L Package information



TOP VIEW
[顶视图]



BOTTOM VIEW
[背视图]



SIDE VIEW
[侧视图]

Symbol	Dimensions in Millimeters(mm)		Dimensions in Inches	
	Min	Max	Min	Max
A	0.600	0.700	0.023	0.027
A1	0.000	0.050	0.000	0.001
A3	0.203REF		0.007REF	
b	0.315	0.415	0.012	0.016
D	1.924	2.076	0.075	0.081
E	1.924	2.076	0.075	0.081
e	0.650TYP		0.225TYP	
L	0.224	0.376	0.008	0.014
k	0.200	-	0.007	-
E1	1.000	1.200	0.039	0.047
D1	0.900	1.100	0.035	0.043
E2	0.700	0.900	0.027	0.035
D2	0.150	0.350	0.005	0.013